

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

## TK6R7P06PL

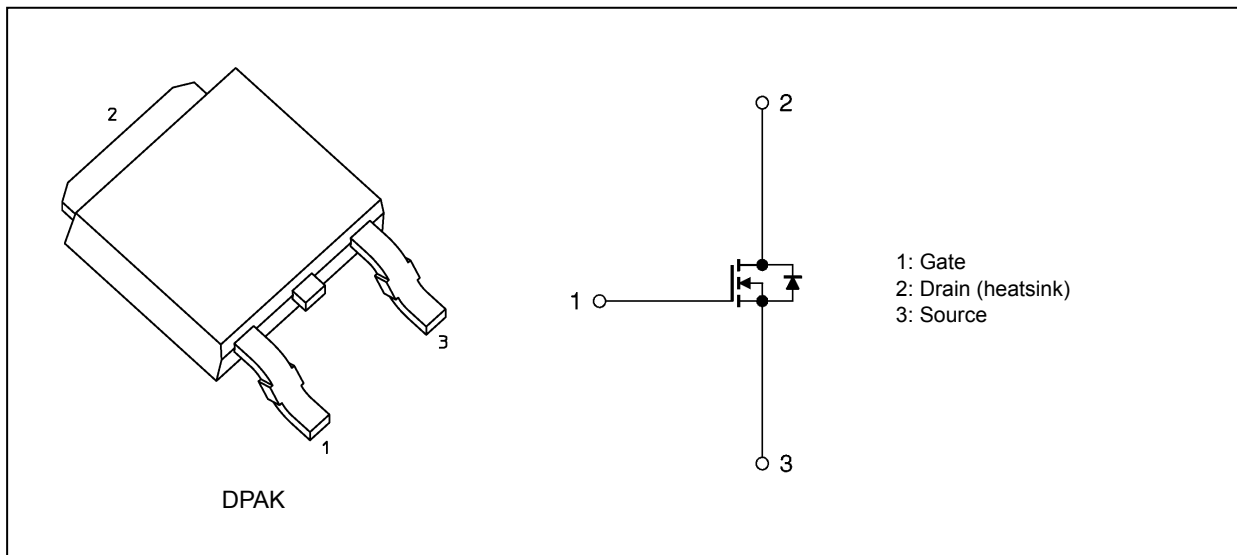
### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 8.7 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{OSS} = 23 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 5.0 \text{ m}\Omega \text{ (typ.) (} V_{GS} = 10 \text{ V)}$
- (5) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max) (} V_{DS} = 60 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.5 \text{ to } 2.5 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 0.3 \text{ mA)}$

### 3. Packaging and Internal Circuit



Start of commercial production  
2017-04

## 4. Absolute Maximum Ratings (Note) ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	60	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC) ( $T_c = 25\text{ }^\circ\text{C}$ ) (Note 1)	$I_D$	46	A
Drain current (DC) (Silicon limit) (Note 1), (Note 2)	$I_D$	74	
Drain current (pulsed) ( $t = 100\text{ }\mu\text{s}$ ) (Note 1)	$I_{DP}$	190	
Power dissipation ( $T_c = 25\text{ }^\circ\text{C}$ )	$P_D$	66	W
Single-pulse avalanche energy (Note 3)	$E_{AS}$	14	mJ
Single-pulse avalanche current (Note 3)	$I_{AS}$	46	A
Channel temperature	$T_{ch}$	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 175	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ( $T_c = 25\text{ }^\circ\text{C}$ )	$R_{th(ch-c)}$	2.24	$^\circ\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed  $175\text{ }^\circ\text{C}$ .

Note 2: Limited 46 A by package capability

Note 3:  $V_{DD} = 48\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (initial),  $L = 5.3\text{ }\mu\text{H}$ ,  $I_{AS} = 46\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 0.1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	60	—	—	V
Drain-source breakdown voltage (Note 4)	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	45	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 0.3\text{ mA}$	1.5	—	2.5	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	—	7.5	11.1	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}, I_D = 23\text{ A}$	—	5.0	6.7	

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1990	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	45	—	
Output capacitance	$C_{oss}$		—	350	—	
Gate resistance	$r_g$	—	—	2.0	—	$\Omega$
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	5	—	ns
Switching time (turn-on time)	$t_{on}$		—	16	—	
Switching time (fall time)	$t_f$		—	10	—	
Switching time (turn-off time)	$t_{off}$		—	35	—	

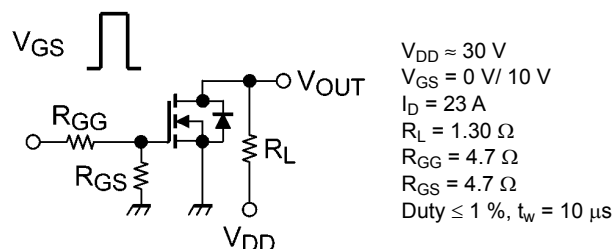


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$	—	26	—	nC
		$V_{DD} \approx 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 23\text{ A}$	—	13	—	
Gate-source charge 1	$Q_{gs1}$	$V_{DD} \approx 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$	—	7.9	—	
Gate-drain charge	$Q_{gd}$		—	4.6	—	
Gate switch charge	$Q_{SW}$		—	8.7	—	
Output charge	$Q_{oss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	23	—	

### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ °C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 5)	$I_{DRP}$ ( $t = 100\ \mu\text{s}$ )	—	—	—	190	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = 46\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 11.5\text{ A}, V_{GS} = 0\text{ V},$ $-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	31	—	ns
Reverse recovery charge	$Q_{rr}$		—	25	—	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking

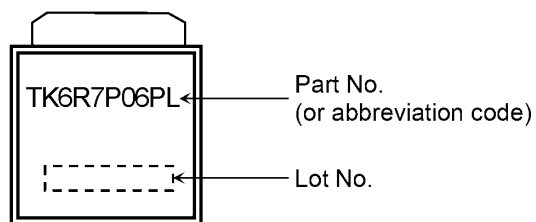


Fig. 7.1 Marking

## 8. Characteristics Curves (Note)

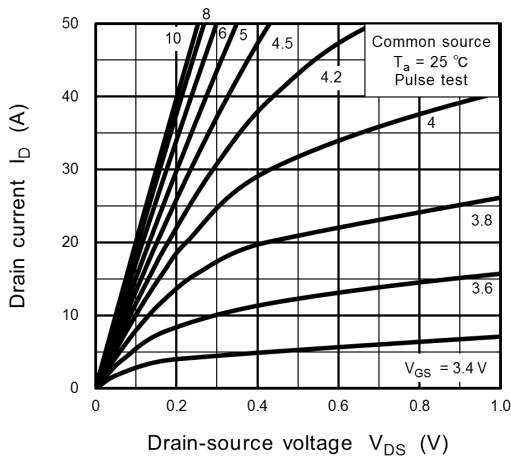


Fig. 8.1  $I_D - V_{DS}$

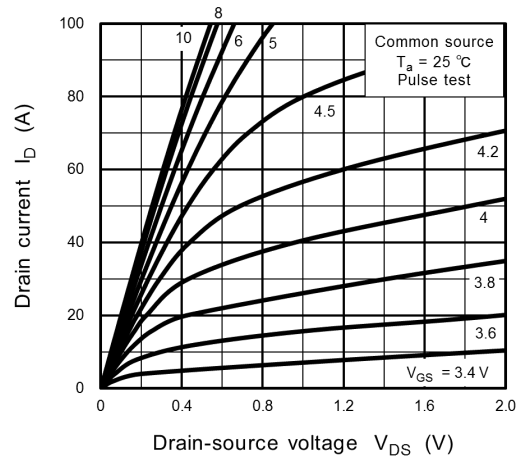


Fig. 8.2  $I_D - V_{DS}$

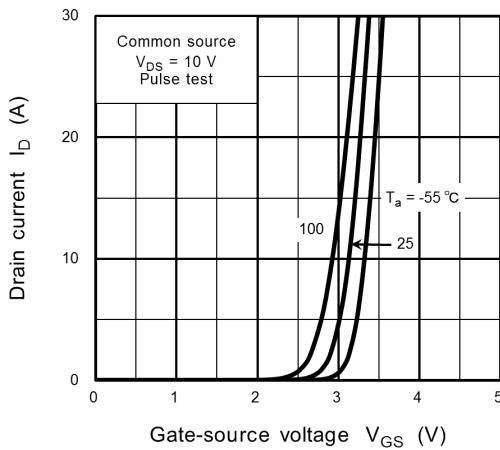


Fig. 8.3  $I_D - V_{GS}$

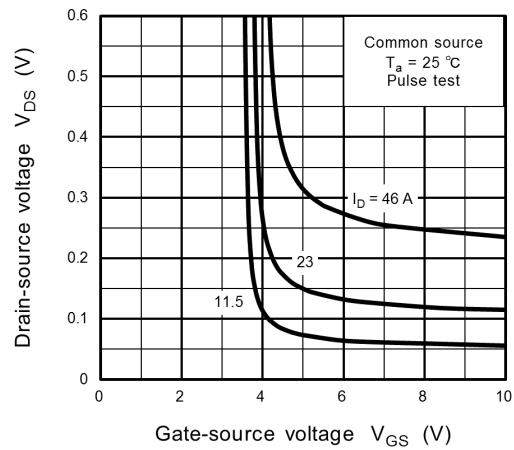


Fig. 8.4  $V_{DS} - V_{GS}$

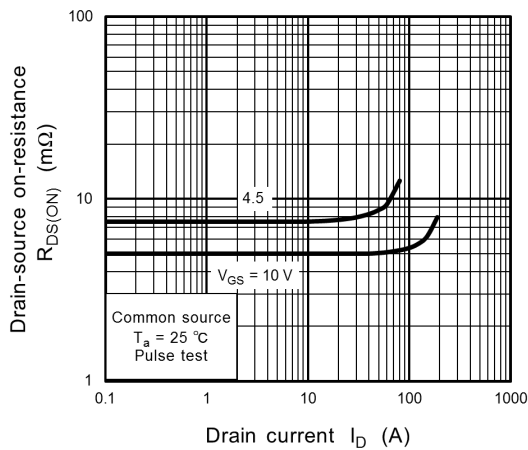


Fig. 8.5  $R_{DS(ON)} - I_D$

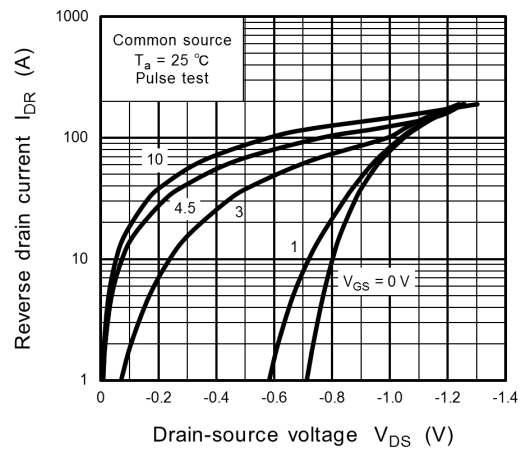
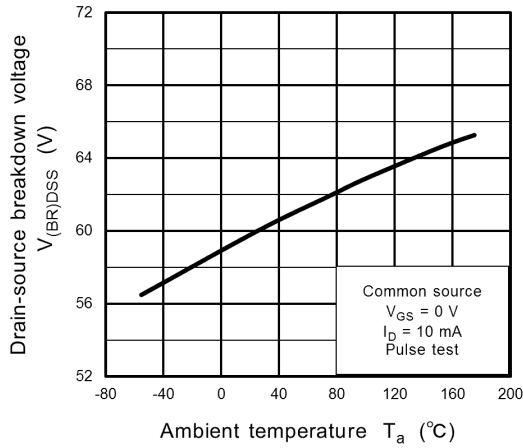
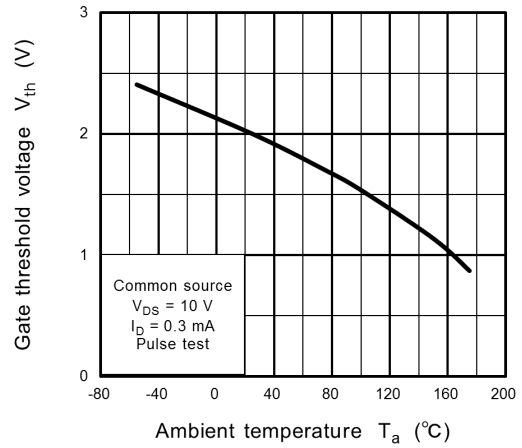


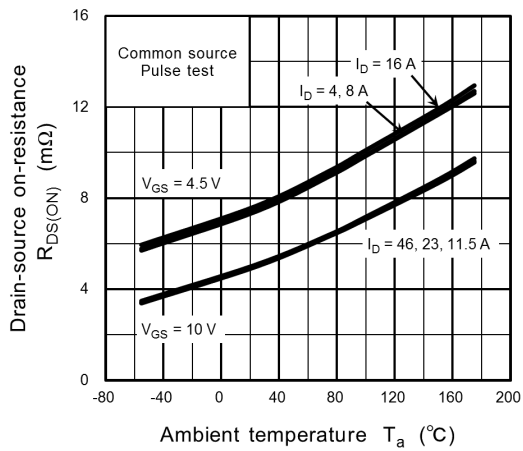
Fig. 8.6  $I_{DR} - V_{DS}$



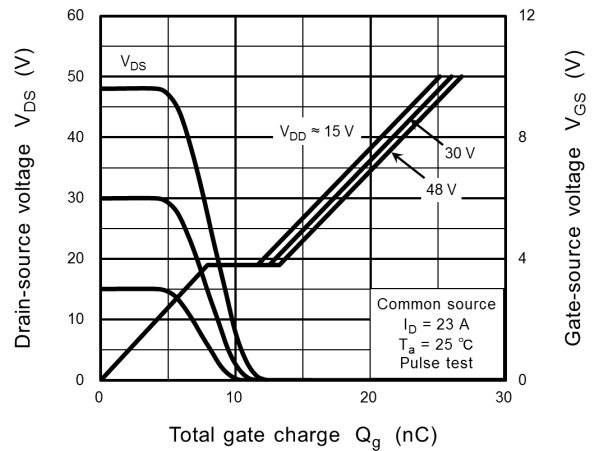
**Fig. 8.7**  $V_{(BR)DSS} - T_a$



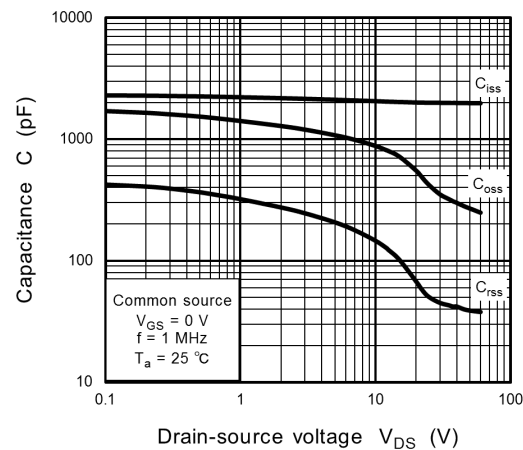
**Fig. 8.8**  $V_{th} - T_a$



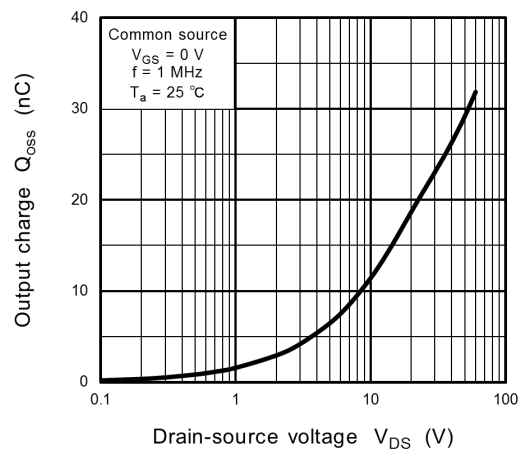
**Fig. 8.9**  $R_{DS(ON)} - T_a$



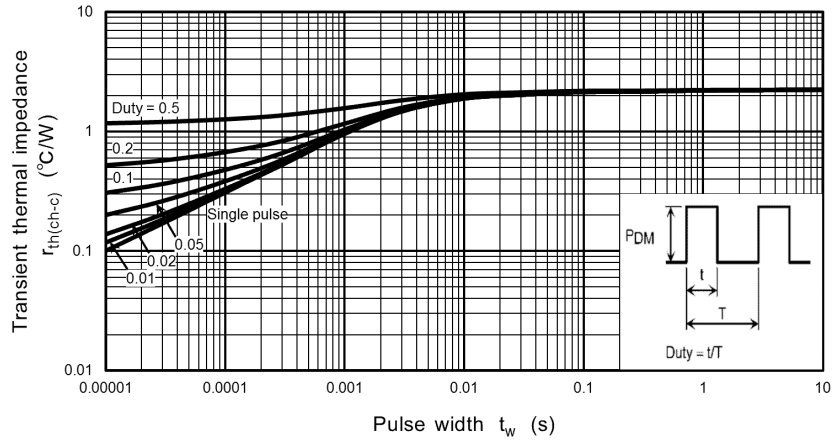
**Fig. 8.10** Dynamic Input/Output Characteristics



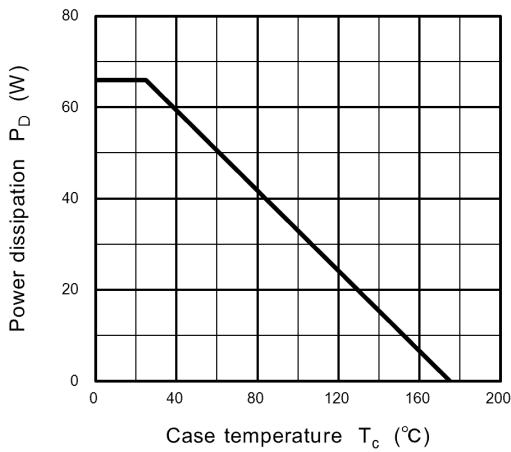
**Fig. 8.11** Capacitance -  $V_{DS}$



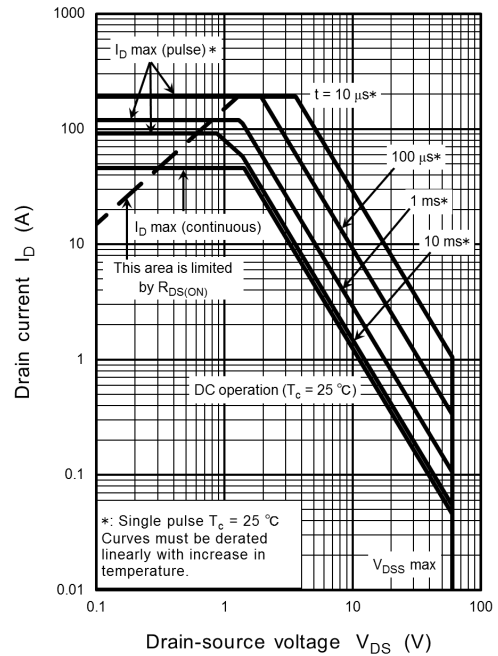
**Fig. 8.12**  $Q_{oss} - V_{DS}$



**Fig. 8.13  $r_{th} - t_w$   
(Guaranteed Maximum)**



**Fig. 8.14  $P_D - T_c$   
(Guaranteed Maximum)**

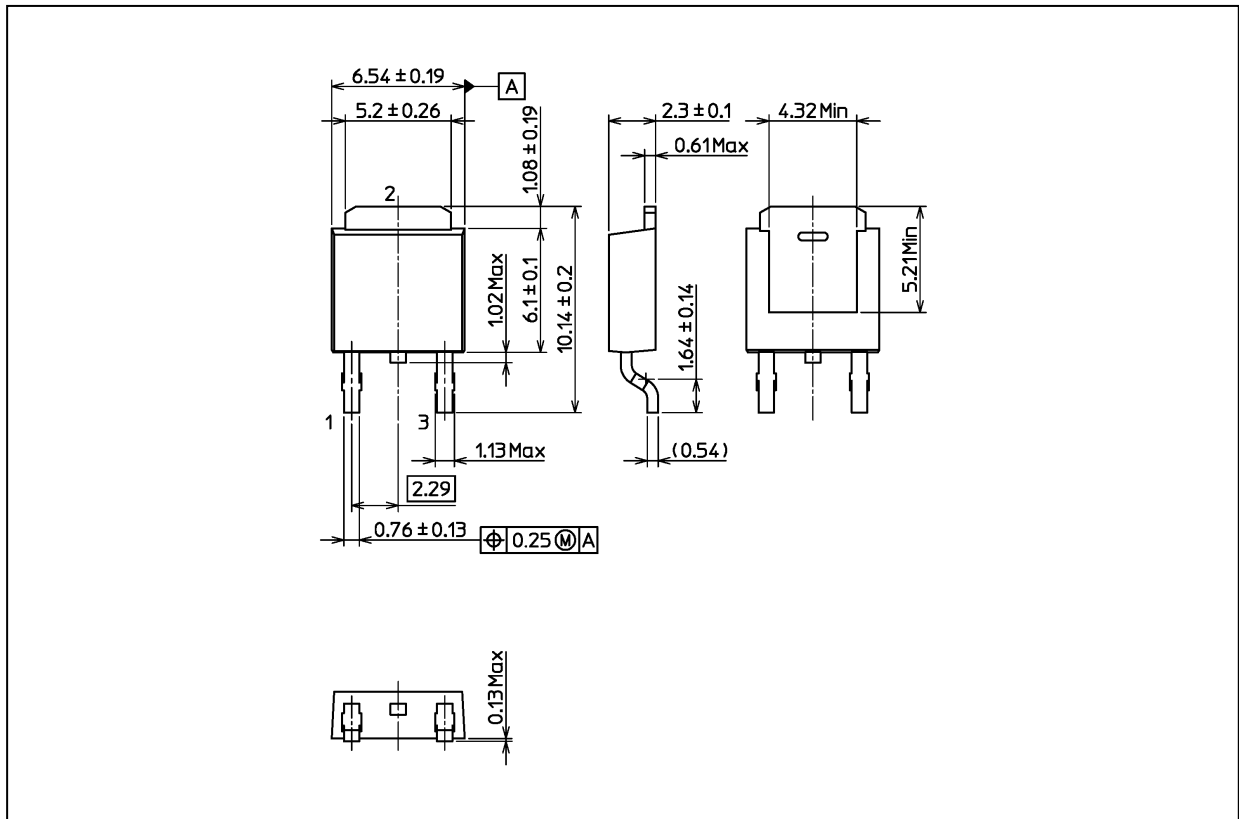


**Fig. 8.15 Safe Operating Area  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.33 g (typ.)

Package Name(s)
TOSHIBA: 2-7N1S
Nickname: DPAK

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